# High Frequency 100 mA CMOS Charge Pump, Inverter/Doubler

#### Description

The CAT661 is a charge-pump voltage converter. It can invert a positive input voltage to a negative output. Only two external capacitors are needed. With a guaranteed 100 mA output current capability, the CAT661 can replace a switching regulator and its inductor. Lower EMI is achieved due to the absence of an inductor.

In addition, the CAT661 can double a voltage supplied from a battery or power supply. Inputs from 2.5 V to 5.5 V will yield a doubled, 5 V to 11 V output.

A Frequency Control pin (BOOST/FC) is provided to select either a high (typically 135 kHz) or low (25 kHz) internal oscillator frequency, thus allowing quiescent current vs. capacitor size trade–offs to be made. The 135 kHz frequency is selected when the FC pin is connected to V+. The operating frequency can also be adjusted with an external capacitor at the OSC pin or by driving OSC with an external clock.

8-pin SOIC package is available. For die availability, contact ON Semiconductor marketing.

The CAT661 can replace the MAX660 and the LTC660 in applications where higher oscillator frequency and smaller capacitors are needed. In addition, the CAT661 is pin compatible with the 7660/1044, offering an easy upgrade for applications with 100 mA loads.

#### Features

- Converts V+ to V- or V+ to 2V+
- Low Output Resistance,  $10 \Omega$  Max.
- High Power Efficiency
- Selectable Charge Pump Frequency of 25 kHz or 135 kHz; Optimize Capacitor Size
- Low Quiescent Current
- Pin-compatible to MAX660, LTC660 with Higher Frequency Operation
- Available in 8-pin SOIC Package
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### Applications

- Negative Voltage Generator
- Voltage Doubler
- Voltage Splitter
- Low EMI Power Source
- GaAs FET Biasing
- Lithium Battery Power Supply
- Instrumentation
- LCD Contrast Bias
- Cellular Phones, Pagers



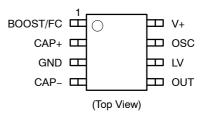
# **ON Semiconductor®**

http://onsemi.com

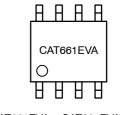


SOIC-8 V SUFFIX CASE 751BD

#### **PIN CONFIGURATION**







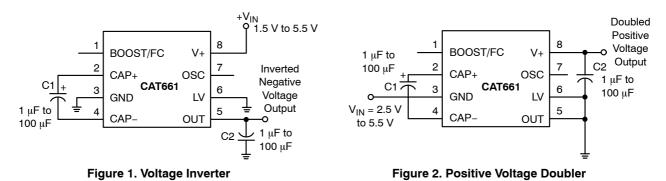
CAT661EVA = CAT661EVA-GT3

#### **ORDERING INFORMATION**

Device	Package	Shipping
CAT661EVA-GT3	SOIC-8 (Pb-Free)	3,000 / Tape & Reel

- 1. All packages are RoHS-compliant (Lead-free, Halogen-free).
- For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
- For detailed information and a breakdown of device nomenclature and numbering systems, please see the ON Semiconductor Device Nomenclature document, TND310/D, available at www.onsemi.com

# **Typical Application**



#### Table 1. PIN DESCRIPTIONS

		Circuit Configuration				
Pin Number	Name		Inverter Mode	Doubler Mode		
1	Boost/FC	Frequency Control for the internal oscillator. With an external oscillator BOOST/FC has no effect.		Same as inverter.		
		Boost/FC	Oscillator Frequency	Oscillator Frequency		
		Open	25 kHz typical, 10 kHz minimum	40 kHz typical		
		V+	135 kHz typical, 80 kHz minimum	135 kHz typical, 40 kHz minimum		
2	CAP+	Charge Pump Capacitor. Positive terminal.		Same as inverter.		
3	GND	Power Supply Gr	ound.	Power supply. Positive voltage input.		
4	CAP-	Charge pump ca	pacitor. Negative terminal.	Same as inverter.		
5	OUT	Output for negative voltage.		Power supply ground.		
6	LV	than 3 V, connec	ection pin. When the input voltage is less t LV to GND. For input voltages above 3 V, ected to GND or left open. If OSC is driven ct LV to GND.	LV must be tied to OUT for all input voltages.		
7	OSC	ted to lower the c can drive OSC a	input. An external capacitor can be connec- oscillator frequency. An external oscillator nd set the chip operating frequency. The equency is one-half the frequency at OSC.	Same as inverter. Do not overdrive OSC in doubling mode. Standard logic levels will not be suitable. See the applications section for additional information.		
8	V+	Power supply. Po	ositive voltage input.	Positive voltage output.		

#### Table 2. ABSOLUTE MAXIMUM RATINGS

Parameters	Ratings	Units
V+ to GND	6	V
Input Voltage (Pins 1, 6 and 7)	-0.3 to (V+ + 0.3)	V
BOOST/FC and OSC Input Voltage	The least negative of (Out – 0.3 V) or $(V+ - 6 V)$ to $(V+ + 0.3 V)$	V
Output Short-circuit Duration to GND (OUT may be shorted to GND for 1 sec without damage but shorting OUT to V+ should be avoided.)	1	Sec.
Continuous Power Dissipation (T <sub>A</sub> = 70°C) Plastic DIP SO TDFN	730 500 1	mW mW W
Storage Temperature	-65 to +160	°C
Lead Soldering Temperature (10 sec)	300	°C
ESD Rating – Human Body Model	2000	V
Operating Ambient Temperature Range	-40 to +85	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

NOTE: T<sub>A</sub> = Ambient Temperature

**Table 3. ELECTRICAL CHARACTERISTICS** (V+ = 5 V, C1 = C2 = 100  $\mu$ F, Boost/FC = Open, C<sub>OSC</sub> = 0 pF, and Test Circuit is Figure 3 unless otherwise noted. Temperature is T<sub>A</sub> = T<sub>AMIN</sub> to T<sub>AMAX</sub> unless otherwise noted.)

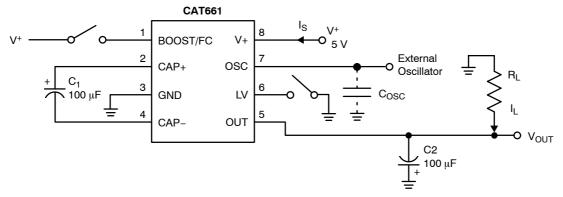
Parameter	Symbol	Conditions	Min	Тур	Max	Units
Supply Voltage	VS	Inverter: LV = Open, $R_L = 1 \ k\Omega$	3.0		5.5	V
		Inverter: LV = GND, $R_L$ = 1 k $\Omega$	1.5		5.5	
		Doubler: LV = OUT, R <sub>L</sub> = 1 k $\Omega$	2.5		5.5	
Supply Current	IS	BOOST/FC = open, LV = Open		0.2	0.5	mA
		BOOST/FC = V+, LV = Open		1	3	
Output Current	IOUT	OUT is more negative than -4 V	100			mA
Output Resistance	RO	$\begin{array}{l} C1 = C2 = 10 \ \mu F \\ BOOST/FC = V+ \ (C1, \ C2 \ ESR \leq 0.5 \ \Omega) \end{array}$		3.5	10	Ω
		C1 = C2 = 100 µF (Note 5)		3.5	10	
Oscillator Frequency	FOSC	BOOST/FC = Open	10	25		kHz
(Note 6)		BOOST/FC = V+	80	135		
OSC Input Current	IOSC	BOOST/FC = Open BOOST/FC = V+		±2 ±10		μΑ
Power Efficiency F	PE	$R_L$ = 1 k $\Omega$ connected between V+ and OUT, T <sub>A</sub> = 25°C (Doubler)	96	98		%
		$R_L$ = 500 $\Omega$ connected between GND and OUT, $T_A$ = 25°C (Inverter)	92	96		1
		$I_L$ = 100 mA to GND, $T_A$ = 25°C (Inverter)	1	88		1
Voltage Conversion Efficiency	VEFF	No load, $T_A = 25^{\circ}C$	99	99.9		%

4. In Figure 3, test circuit electrolytic capacitors C1 and C2 are 100 μF and have 0.2 Ω maximum ESR. Higher ESR levels may reduce efficiency and output voltage.

5. The output resistance is a combination of the internal switch resistance and the external capacitor ESR. For maximum voltage and efficiency keep external capacitor ESR under 0.2 Ω.

 FOSC is tested with C<sub>OSC</sub> = 100 pF to minimize test fixture loading. The test is correlated back to C<sub>OSC</sub> = 0 pF to simulate the capacitance at OSC when the device is inserted into a test socket without an external C<sub>OSC</sub>.

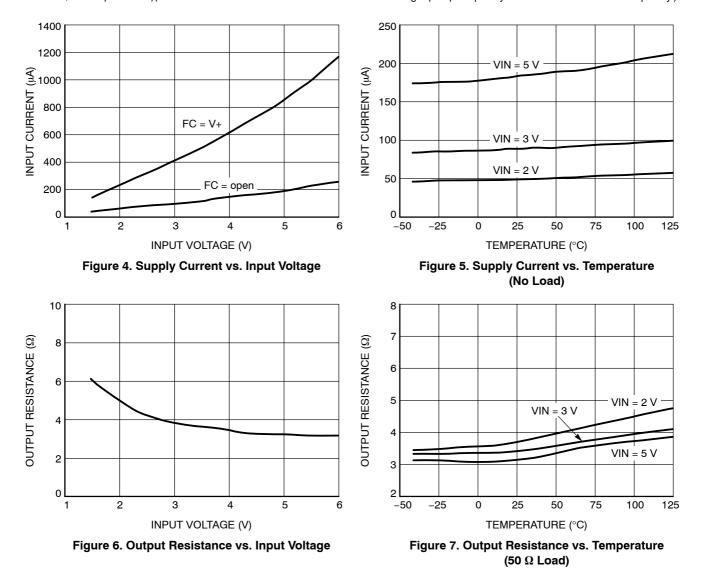
## Voltage Inverter



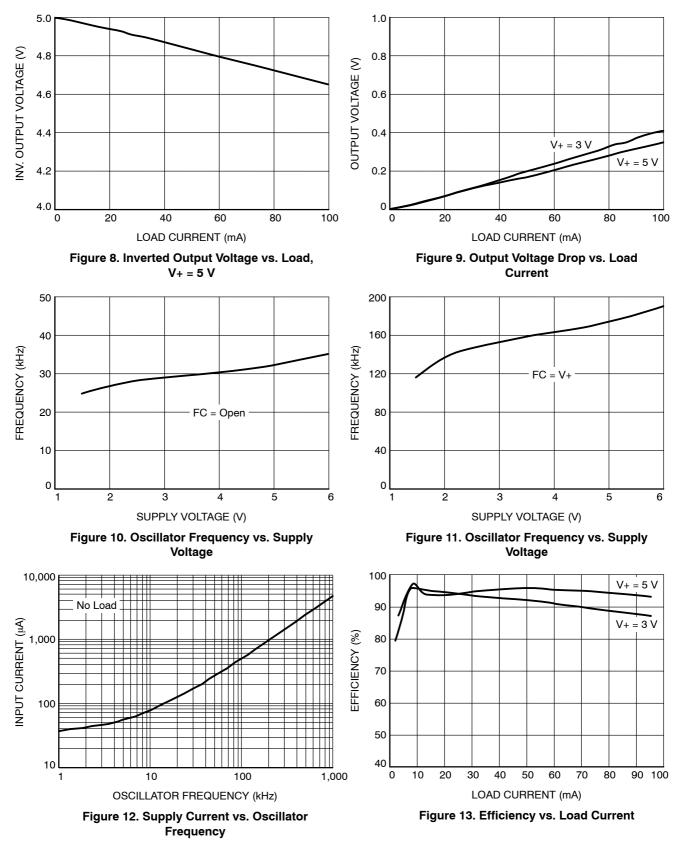


#### **TYPICAL OPERATING CHARACTERISTICS**

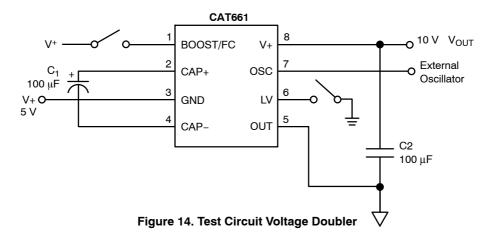
(Typical characteristic curves are generated using the test circuit in Figure 3. Inverter test conditions are:  $V_{+} = 5 V$ , LV = GND, BOOST/FC = Open and  $T_{A} = 25^{\circ}C$  unless otherwise indicated. Note that the charge-pump frequency is one-half the oscillator frequency.)





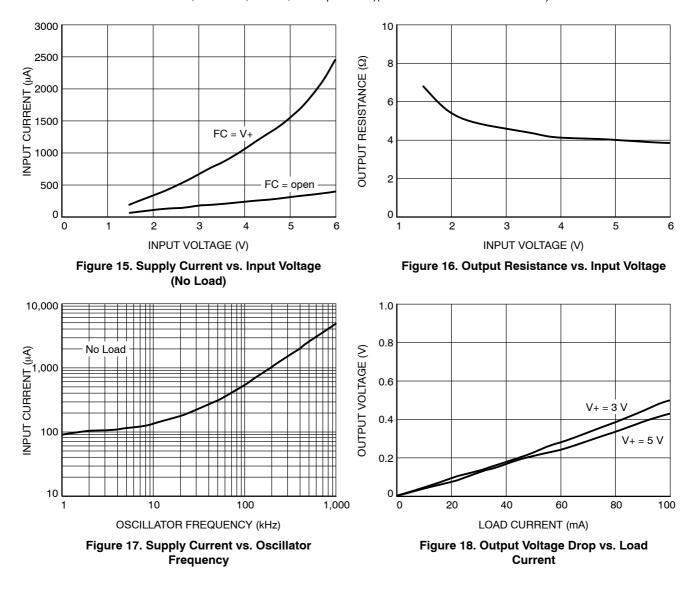


#### Voltage Doubler



TYPICAL OPERATING CHARACTERISTICS

<sup>(</sup>Typical characteristic curves are generated using the circuit in Figure 14. Doubler test conditions are: V+ = 5 V, LV = GND, BOOST/FC = Open and  $T_A = 25^{\circ}C$  unless otherwise indicated.)



### **Application Information**

#### **Circuit Description and Operating Theory**

The CAT661 switches capacitors to invert or double an input voltage.

Figure 19 shows a simple switch capacitor circuit. In position 1 capacitor C1 is charged to voltage V1. The total charge on C1 is Q1 = C1V1. When the switch moves to position 2, the input capacitor C1 is discharged to voltage V2. After discharge, the charge on C1 is Q2 = C1V2.

The charge transferred is:

$$\Delta Q = Q1 - Q2 = C1 \times (V1 - V2)$$

If the switch is cycled "F" times per second, the current (charge transfer per unit time) is:

$$I = F \times \Delta Q = F \times C1 (V1 - V2)$$

Rearranging in terms of impedance:

$$I = \frac{(V1 - V2)}{(1/FC1)} = \frac{V1 - V2}{REQ}$$

The 1/FC1 term can be modeled as an equivalent impedance REQ. A simple equivalent circuit is shown in

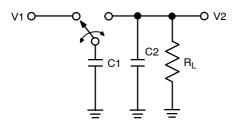


Figure 19. Switched–Capacitor Building Block

Figure 20. This circuit does not include the switch resistance nor does it include output voltage ripple. It does allow one to understand the switch–capacitor topology and make prudent engineering tradeoffs.

For example, power conversion efficiency is set by the output impedance, which consists of REQ and switch resistance. As switching frequency is decreased, REQ, the 1/FC1 term, will dominate the output impedance, causing higher voltage losses and decreased efficiency. As the frequency is increased quiescent current increases. At high frequency this current becomes significant and the power efficiency degrades.

The oscillator is designed to operate where voltage losses are a minimum. With external 150  $\mu$ F capacitors, the internal switch resistances and the Equivalent Series Resistance (ESR) of the external capacitors determine the effective output impedance.

A block diagram of the CAT661 is shown in Figure 21.

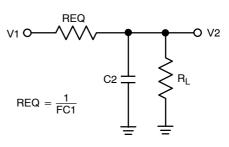


Figure 20. Switched–Capacitor Equivalent Circuit

#### **Oscillator Frequency Control**

The switching frequency can be raised, lowered or driven from an external source. Figure 22 shows a functional diagram of the oscillator circuit.

The CAT661 oscillator has four control modes:

#### Table 4.

BOOST/FC Pin Connection	OSC Pin Connection	Nominal Oscillator Frequency
Open	Open	25 kHz
BOOST/FC = V+	Open	135 kHz
Open or BOOST/FC = V+	External Capacitor	-
Open	External Clock	Frequency of external clock

If BOOST/FC and OSC are left floating (Open), the nominal oscillator frequency is 25 kHz. The pump frequency is one-half the oscillator frequency.

By connecting the BOOST/FC pin to V+, the charge and discharge currents are increased, and the frequency is increased by approximately 6 times. Increasing the frequency will decrease the output impedance and ripple currents. This can be an advantage at high load currents. Increasing the frequency raises quiescent current but allows smaller capacitance values for C1 and C2.

If pin 7, OSC, is loaded with an external capacitor the frequency is lowered. By using the BOOST/FC pin and an external capacitor at OSC, the operating frequency can be set.

Note that the frequency appearing at CAP+ or CAP- is one-half that of the oscillator.

Driving the CAT661 from an external frequency source can be easily achieved by driving Pin 7 and leaving the BOOST pin open, as shown in Figure 22. The output current from Pin 7 is small, typically 1  $\mu$ A to 8  $\mu$ A, so a CMOS can drive the OSC pin. For 5 V applications, a TTL logic gate can be used if an external 100 k $\Omega$  pull–up resistor is used as shown in Figure 23.

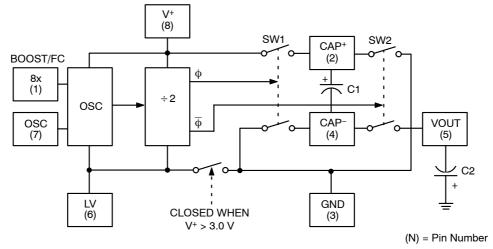


Figure 21. CAT661 Block Diagram

#### **Capacitor Selection**

Low ESR capacitors are necessary to minimize voltage losses, especially at high load currents. The exact values of C1 and C2 are not critical but low ESR capacitors are necessary.

The ESR of capacitor C1, the pump capacitor, can have a pronounced effect on the output. C1 currents are approximately twice the output current and losses occur on both the charge and discharge cycle. The ESR effects are thus multiplied by four. A 0.5  $\Omega$  ESR for C1 will have the same effect as a 2  $\Omega$  increase in CAT661 output impedance.

Output voltage ripple is determined by the value of C2 and the load current. C2 is charged and discharged at a current roughly equal to the load current. The internal switching frequency is one-half the oscillator frequency.

 $VRIPPLE = IOUT/(FOSC \times C2) + IOUT \times ESRC2$ 

For example, with a 25 kHz oscillator frequency (12.5 kHz switching frequency), a 150  $\mu$ F C2 capacitor with an ESR of 0.2  $\Omega$  and a 100 mA load peak-to-peak ripple voltage is 45 mV.

Table 5. VRIPPLE vs. FOSC

VRIPPLE (mV)	IOUT (mA)	FOSC (kHz)	C2 (µF)	C2 ESR (Ω)
45	100	25	150	0.2
25	100	135	150	0.2

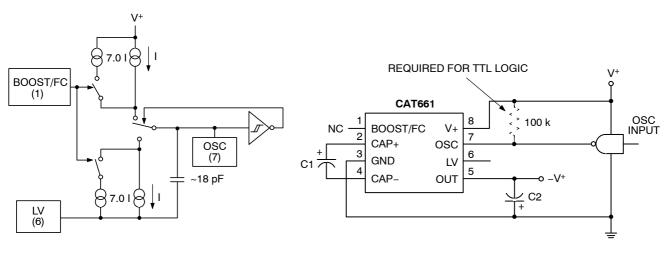


Figure 22. Oscillator

Figure 23. External Clocking

#### **Capacitor Suppliers**

The following manufacturers supply low-ESR capacitors:

#### Table 6. CAPACITOR SUPPLIERS

Manufacturer	Capacitor Type	Phone	WEB	Email	Comments
AVX/Kyocera	TPS/TPS3	843-448-9411	www.avxcorp.com	avx@avxcorp.com	Tantalum
Vishay/Sprague	595	402-563-6866	www.vishay.com	-	Aluminum
Sanyo	MV-AX, UGX	619-661-6835	www.sanyo.com	Svcsales@sanyo.com	Aluminum
Nichicon	F55	847-843-7500	www.nichicon-us.com	-	Tantalum
	HC/HD				Aluminum

Capacitor manufacturers continually introduce new series and offer different package styles. It is recommended that before a design is finalized capacitor manufacturers should be surveyed for their latest product offerings.

#### **Controlling Loss in CAT661 Applications**

There are three primary sources of voltage loss:

1. Output resistance:

VLOSS = ILOAD x ROUT, where ROUT is the CAT661 output resistance and ILOAD is the load current.

2. Charge pump (C1) capacitor ESR:

VLOSSC1  $\approx$  4 x ESRC1 x ILOAD, where ESRC1 is the ESR of capacitor C1.

3. Output or reservoir (C2) capacitor ESR:

VLOSSC2 = ESRC2 x ILOAD, where ESRC2 is the ESR of capacitor C2.

Increasing the value of C2 and/or decreasing its ESR will reduce noise and ripple.

The effective output impedance of a CAT661 circuit is approximately:

Rcircuit  $\approx$  Rout 661 + (4 × ESRC1) + ESRC2

# **Typical Applications**

#### Voltage Inversion Positive-to-Negative

The CAT661 easily provides a negative supply voltage from a positive supply in the system. Figure 24 shows a typical circuit. The LV pin may be left floating for positive input voltages at or above 3.3 V.

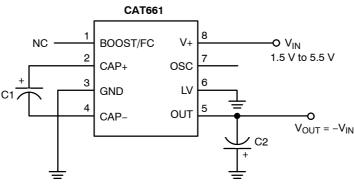


Figure 24. Voltage Inverter

#### **Positive Voltage Doubler**

The voltage doubler circuit shown in Figure 25 gives  $V_{OUT} = 2 \times V_{IN}$  for input voltages from 2.5 V to 5.5 V.

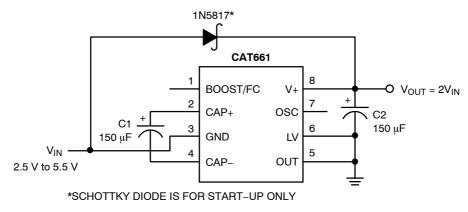


Figure 25. Voltage Doubler

#### **Precision Voltage Divider**

A precision voltage divider is shown in Figure 26. With load currents under 100 nA, the voltage at pin 2 will be within 0.002% of V+/2.

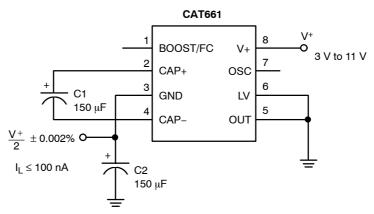
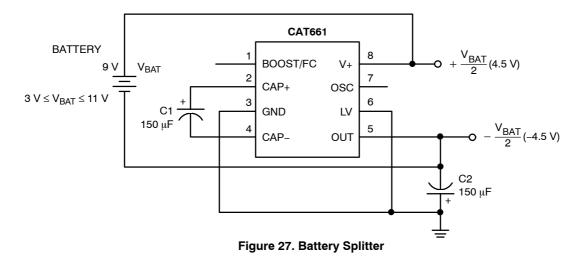


Figure 26. Precision Voltage Divider (Load ≤ 100 nA)

#### **Battery Voltage Splitter**

Positive and negative voltages that track each other can be obtained from a battery. Figure 27 shows how a 9 V battery can provide symmetrical positive and negative voltages equal to one-half the battery voltage.



#### **Cascade Operation for Higher Negative Voltages**

The CAT661 can be cascaded as shown in Figure 28 to generate more negative voltage levels. The output resistance is approximately the sum of the individual CAT661 output resistance.

 $V_{OUT} = -N \times V_{IN}$ , where N represents the number of cascaded devices.

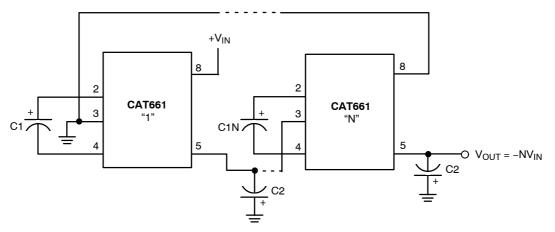


Figure 28. Cascading to Increase Output Voltage

#### **Parallel Operation**

Paralleling CAT661 devices will lower output resistance. As shown in Figure 29, each device requires its own pump capacitor, C2, but the output reservoir capacitor is shared with all devices. The value of C2 should be increased by a factor of N, where N is the number of devices.

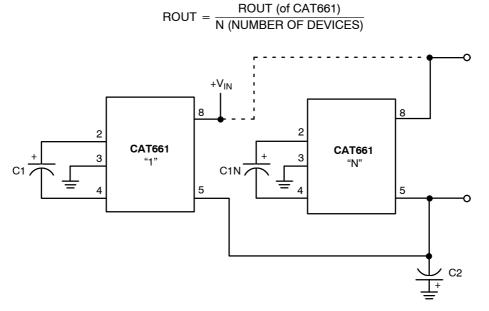
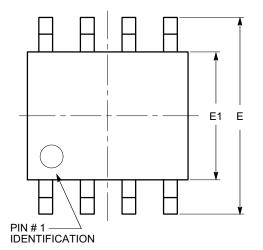


Figure 29. Reduce Output Resistance BY Paralleling Devices

# **Onsem**í.

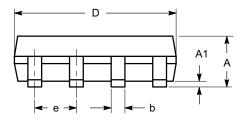
SOIC-8, 150 mils CASE 751BD ISSUE O

DATE 19 DEC 2008



TOP VIEW

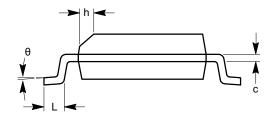
SYMBOL	MIN	NOM	MAX
А	1.35		1.75
A1	0.10		0.25
b	0.33		0.51
с	0.19		0.25
D	4.80		5.00
E	5.80		6.20
E1	3.80		4.00
е		1.27 BSC	
h	0.25		0.50
L	0.40		1.27
θ	0°		8°



SIDE VIEW

#### Notes:

(1) All dimensions are in millimeters. Angles in degrees.
(2) Complies with JEDEC MS-012.



END VIEW

DOCUMENT NUMBER:	98AON34272E	4272E Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.							
DESCRIPTION:	SOIC 8, 150 MILS PAGE 1 OF								
the right to make changes without furth purpose, nor does <b>onsemi</b> assume an	er notice to any products herein. <b>onsemi</b> mak ny liability arising out of the application or use	es no warranty, representation or guarantee regarding the suitability of its pro of any product or circuit, and specifically disclaims any and all liability, incl	onsemi and ONSEMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights or the rights of others.						

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent\_Marking.pdf</u>. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or indental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification. Buyer shall indemnify and hold onsemi and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs,

#### ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation onsemi Website: www.onsemi.com

ONLINE SUPPORT: <u>www.onsemi.com/support</u> For additional information, please contact your local Sales Representative at <u>www.onsemi.com/support/sales</u>